

FIG. 1

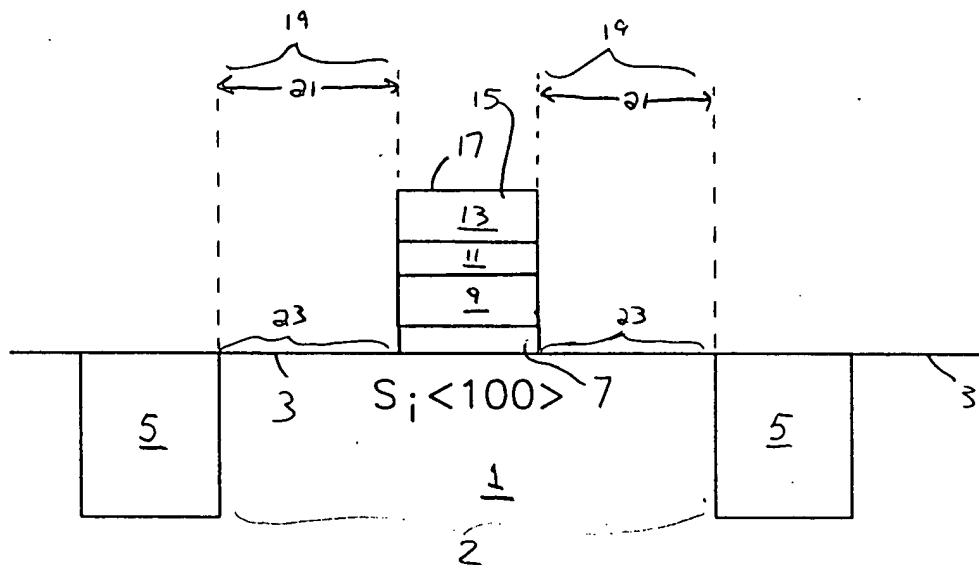


FIG. 2

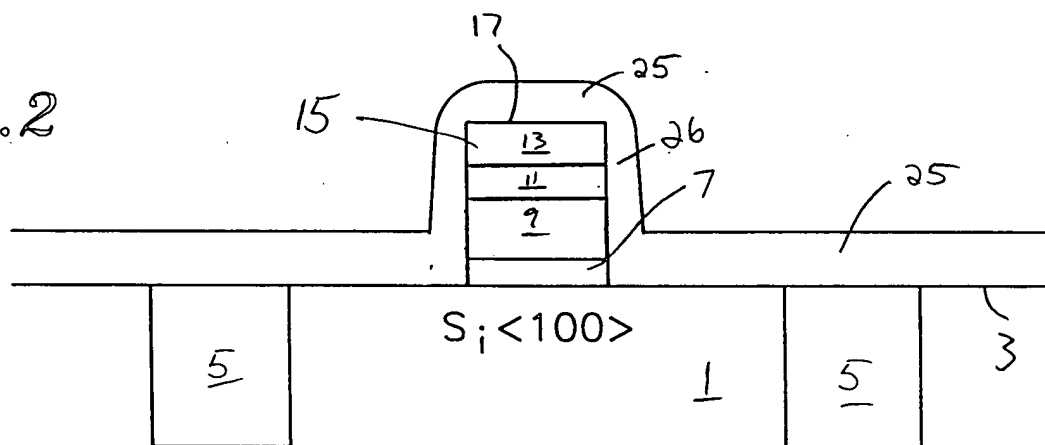


FIG. 3

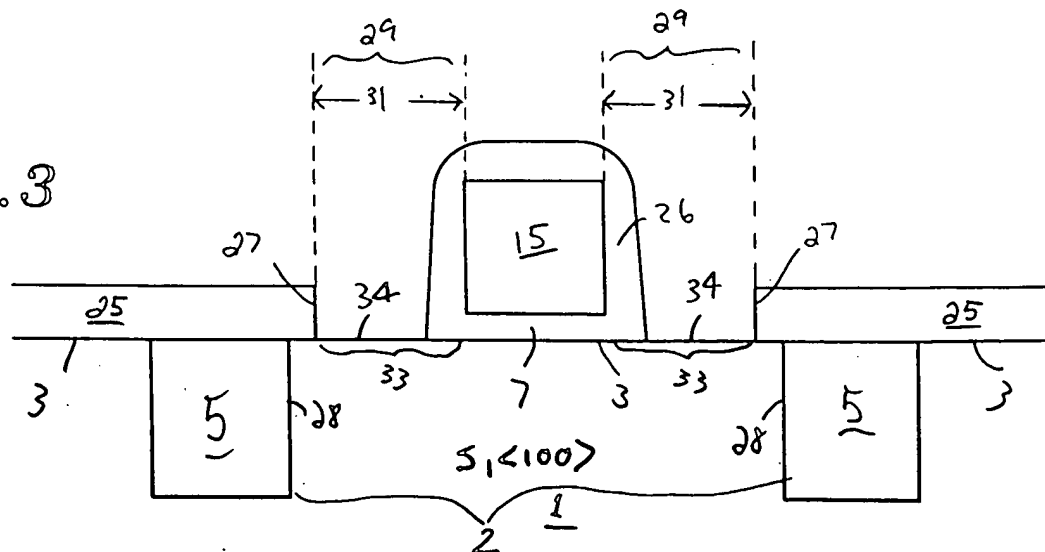


FIG. 6

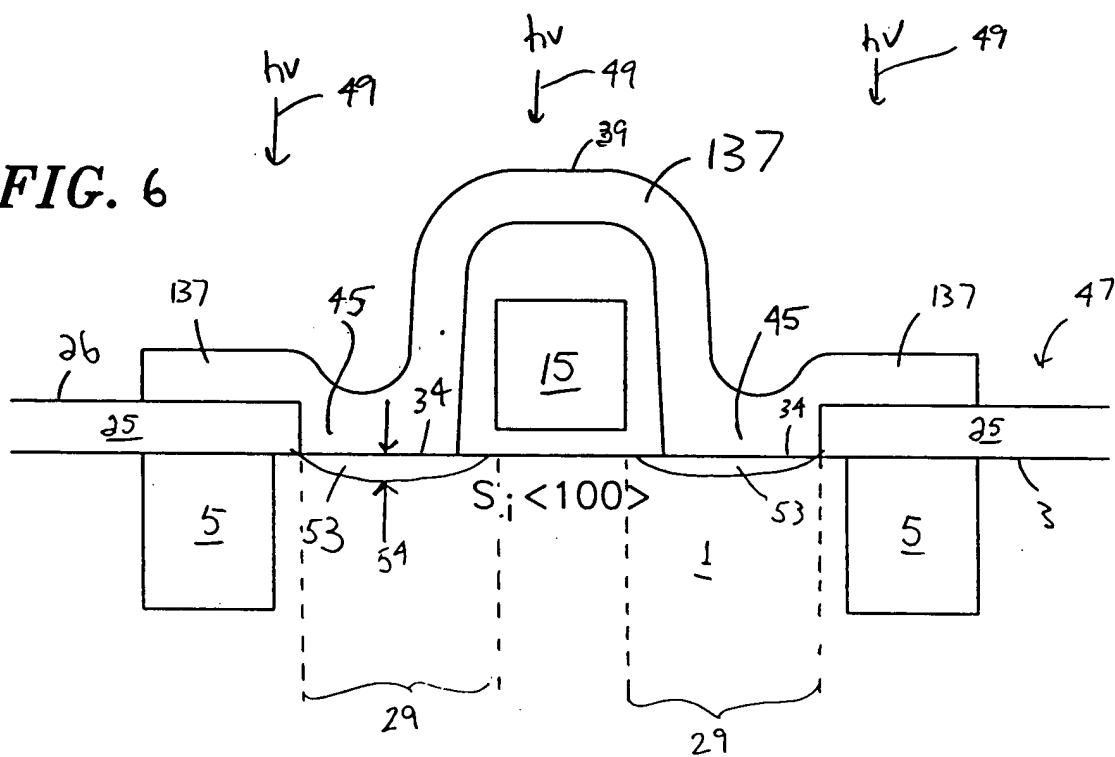


FIG. 8

FIG. 8 is a cross-sectional view of a semiconductor device. The device features a substrate 3 with a layer 5 on top. A central region 15 is surrounded by a layer 17. The device is divided into two symmetrical halves by a central vertical dashed line 61. Each half contains a structure 59 with a wavy interface 55. Dimensions are indicated: 67 for the width of the central region, 69 for the width of the side regions, 63 for the height of the side regions, 137 for the width of the central region, 34 for the width of the side regions, 53 for the width of the central region, and 57 for the width of the side regions. The material is labeled Si<100>.